

General Purpose Transistor

PNP Silicon

MMBT2907AWT1G, NSVMMBT2907AWT1G

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-60	Vdc
Collector - Base Voltage	V_{CBO}	-60	Vdc
Emitter – Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	Ic	-600	mAdc

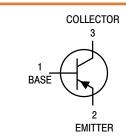
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C	P _D	150	mW
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	833	°C/W
Junction and Storage Temperature	T _J , T _{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.





SC -70/SOT-323 CASE 419 - 04 STYLE 3

MARKING DIAGRAM



20 = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT2907AWT1G	SC-70 (Pb-Free)	3000 Tape & Reel
NSVMMBT2907AWT1G	SC-70 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Charac	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					l.
Collector – Emitter Breakdown Voltage (Note $(I_C = -10 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	-60	_	Vdc	
Collector – Base Breakdown Voltage (I _C = –10 μAdc, I _E = 0)		V _{(BR)CBO}	-60	_	Vdc
Emitter – Base Breakdown Voltage ($I_E = -10 \mu Adc, I_C = 0$)		V _{(BR)EBO}	-5.0	-	Vdc
Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)		I _{BL}	-	-50	nAdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)		I _{CEX}	ı	-50	nAdc
ON CHARACTERISTICS(3)		•		•	•
$\begin{array}{l} DC \ Current \ Gain \ (Note \ 2) \\ (I_C = -0.1 \ mAdc, \ V_{CE} = -10 \ Vdc) \\ (I_C = -1.0 \ mAdc, \ V_{CE} = -10 \ Vdc) \\ (I_C = -10 \ mAdc, \ V_{CE} = -10 \ Vdc) \\ (I_C = -150 \ mAdc, \ V_{CE} = -10 \ Vdc) \\ (I_C = -500 \ mAdc, \ V_{CE} = -10 \ Vdc) \end{array}$	H _{FE}	75 100 100 100 50	- - - 340 -	-	
Collector – Emitter Saturation Voltage (Note 2 (I_C = -150 mAdc, I_B = -15 mAdc) (I_C = -500 mAdc, I_B = -50 mAdc)	V _{CE(sat)}	- -	-0.4 -1.6	Vdc	
Base – Emitter Saturation Voltage (Note 2) (I_C = -150 mAdc, I_B = -15 mAdc) (I_C = -500 mAdc, I_B = -50 mAdc)	V _{BE(sat)}	- -	-1.3 -2.6	Vdc	
SMALL-SIGNAL CHARACTERISTICS				•	
Current – Gain – Bandwidth Product (I _C = –50 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)		f _T	200	_	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = -2.0 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	ı	30	pF	
SWITCHING CHARACTERISTICS					
Turn-On Time		t _{on}	-	45	
Delay Time	$(V_{CC} = -30 \text{ Vdc}, I_{C} = -150 \text{ mAdc}, I_{B1} = -15 \text{ mAdc})$	t _d	-	10	
Rise Time		t _r	I	40	no
Storage Time		t _s	_	80	ns
Fall Time	$(V_{CC} = -6.0 \text{ Vdc}, I_{C} = -150 \text{ mAdc}, I_{B_1} = I_{B_2} = 15 \text{ mAdc})$	t _f	I	30	
Turn-Off Time	,	t _{off}	-	100	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width $\leq 300 \, \mu s$, Duty Cycle $\leq 2.0\%$.

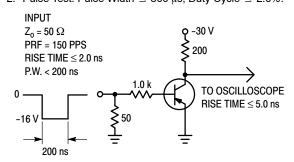


Figure 1. Delay and Rise Time Test Circuit

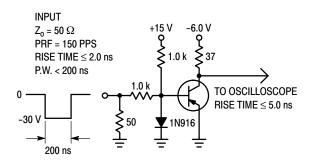


Figure 2. Storage and Fall Time Test Circuit

MMBT2907AWT1G, NSVMMBT2907AWT1G

TYPICAL CHARACTERISTICS

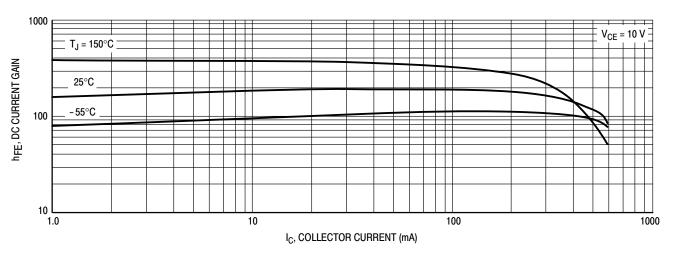


Figure 3. DC Current Gain

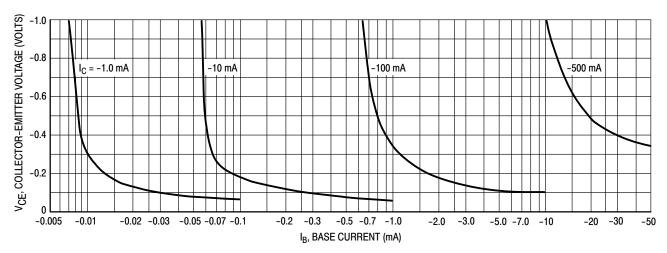


Figure 4. Collector Saturation Region

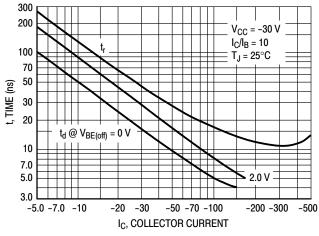


Figure 5. Turn-On Time

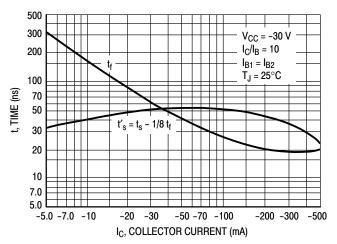


Figure 6. Turn-Off Time

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TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

 V_{CE} = 10 Vdc, T_A = 25°C

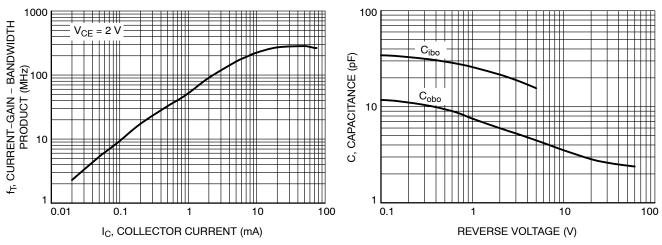


Figure 7. Current-Gain - Bandwidth Product

Figure 8. Capacitances

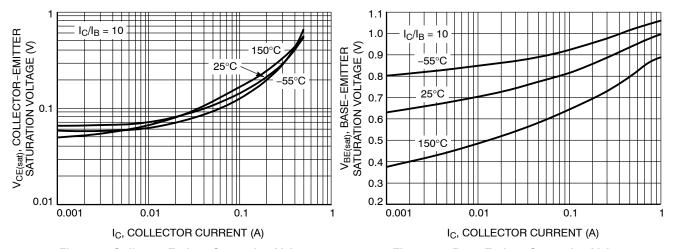


Figure 9. Collector Emitter Saturation Voltage vs. Collector Current

Figure 10. Base Emitter Saturation Voltage vs.
Collector Current

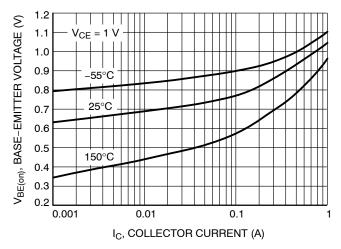


Figure 11. Base Emitter Voltage vs. Collector
Current





SC-70 (SOT-323) **CASE 419** ISSUE R

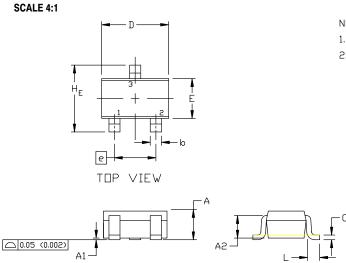
END VIEW

DATE 11 OCT 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS			INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2		0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.00	2.20	0.071	0.080	0.087	
E	1.15	1.24	1.35	0.045	0.049	0.053	
е	1.20	1.30	1.40	0.047	0.051	0.055	
e1	0.65 BSC			0.026 BSC			
L	0.20	0.38	0.56	0.008	0.015	0.022	
HE	2.00	2.10	2.40	0.079	0.083	0.095	



GENERIC MARKING DIAGRAM

SIDE VIEW

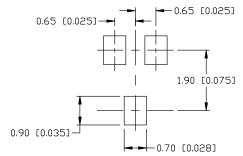


= Specific Device Code XX

М = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6: PIN 1. EMITTER	STYLE 7: PIN 1. BASE	STYLE 8: PIN 1. GATE	STYLE 9: PIN 1. ANODE	STYLE 10: PIN 1. CATHODE	STYLE 11: PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

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